



**THE DATASHEET OF
C3D08060G-TR**



C3D08060G

600 V, 8 A Silicon Carbide Schottky Diode



TO-263-2



Features

- 600-Volt Schottky rectifier
- Zero reverse recovery current
- Zero forward recovery voltage
- High-frequency operation
- Temperature-independent switching behavior
- Extremely fast switching
- Positive temperature coefficient on V_f



Package Types: TO-263-2

PN: C3D08060G

WolfSpeed, Inc. is in the process of rebranding its products and related materials pursuant to the entity name change from Cree, Inc. to WolfSpeed, Inc. During this transition period, products received may be marked with either the Cree name and/or logo or the WolfSpeed name and/or logo.

Applications

- Switch mode power supplies (SMPS)
- Boost diodes in PFC or DC/DC stages
- Free wheeling diodes in inverter stages
- AC/DC converters

Benefits

- Replace bipolar with unipolar rectifiers
- Essentially no switching losses
- Higher efficiency
- Reduction of heat sink requirements
- Parallel devices without thermal runaway

Maximum Ratings ($T_c = 25\text{ }^\circ\text{C}$ Unless Otherwise Specified)

Parameter	Symbol	Value	Unit	Test Conditions	Note
Repetitive Peak Reverse Voltage	V_{RRM}	600	V		
Surge Peak Reverse Voltage	V_{RSM}	600			
DC Blocking Voltage	V_{DC}	600			
Continuous Forward Current	I_F	24	A	$T_c = 25\text{ }^\circ\text{C}$	Fig. 3
		11		$T_c = 135\text{ }^\circ\text{C}$	
		8		$T_c = 152\text{ }^\circ\text{C}$	
Repetitive Peak Forward Surge Current	I_{FRM}	36.5	A	$T_c = 25\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$, Half Sine Wave	Fig. 8
		25.5		$T_c = 110\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$, Half Sine Wave	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	71	A	$T_c = 25\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$, Half Sine Wave	Fig. 8
		60		$T_c = 110\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$, Half Sine Wave	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	650	A	$T_c = 25\text{ }^\circ\text{C}$, $t_p = 10\text{ }\mu\text{s}$, Pulse	Fig. 8
		530		$T_c = 110\text{ }^\circ\text{C}$, $t_p = 10\text{ }\mu\text{s}$, Pulse	
Power Dissipation	P_{tot}	107	W	$T_c = 25\text{ }^\circ\text{C}$	Fig. 4
		46.5		$T_c = 110\text{ }^\circ\text{C}$	
Diode dV/dt Ruggedness	dV/dt	200	V/ns	$V_R = 0\text{--}600\text{ V}$	
i^2t Value	$\int i^2 dt$	25	A^2s	$T_c = 25\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$	
		18		$T_c = 110\text{ }^\circ\text{C}$, $t_p = 10\text{ ms}$	
Operating Junction and Storage Temperature	$T_{j, T_{stg}}$	-55 to +175	$^\circ\text{C}$		



Electrical Characteristics

Parameter	Symbol	Typ.	Max.	Unit	Test Conditions	Note
Forward Voltage	V_F	1.5	1.8	V	$I_F = 8 \text{ A}$, $T_J = 25 \text{ }^\circ\text{C}$	Fig. 1
		2.1	2.4		$I_F = 8 \text{ A}$, $T_J = 175 \text{ }^\circ\text{C}$	
Reverse Current	I_R	8.5	42.5	μA	$V_R = 600 \text{ V}$, $T_J = 25 \text{ }^\circ\text{C}$	Fig. 2
		17	170		$V_R = 600 \text{ V}$, $T_J = 175 \text{ }^\circ\text{C}$	
Total Capacitive Charge	Q_C	20		nC	$V_R = 400 \text{ V}$, $I_F = 8 \text{ A}$ $di/dt = 500 \text{ A}/\mu\text{S}$ $T_J = 25 \text{ }^\circ\text{C}$	Fig. 5
Total Capacitance	C	395		pF	$V_R = 0 \text{ V}$, $T_J = 25 \text{ }^\circ\text{C}$, $f = 1 \text{ MHz}$	Fig. 6
		37			$V_R = 200 \text{ V}$, $T_J = 25 \text{ }^\circ\text{C}$, $f = 1 \text{ MHz}$	
		32			$V_R = 400 \text{ V}$, $T_J = 25 \text{ }^\circ\text{C}$, $f = 1 \text{ MHz}$	
Capacitance Stored Energy	E_C	3.0		μJ	$V_R = 400 \text{ V}$	Fig. 7

Note: This is a majority carrier diode, so there is no reverse recovery charge.

Thermal Characteristics

Parameter	Symbol	Typ.	Unit	Note
Thermal Resistance from Junction to Case	$R_{\theta JC}$	1.4	$^\circ\text{C}/\text{W}$	Fig. 9

Typical Performance

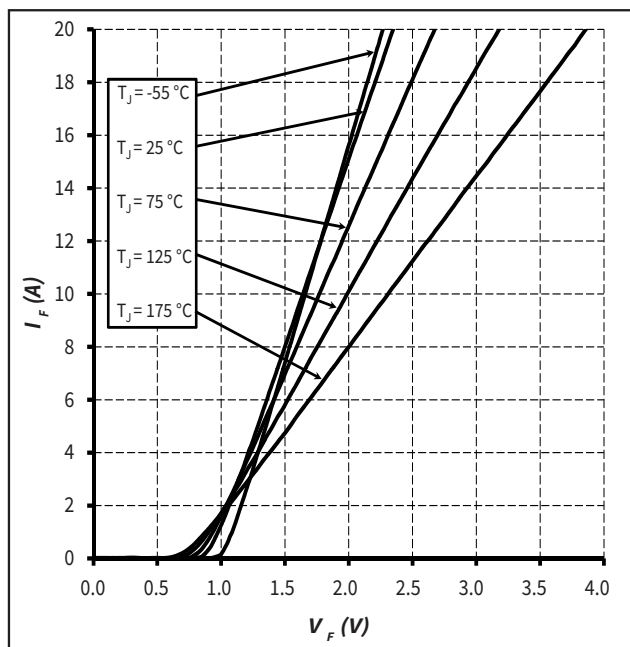


Figure 1. Forward Characteristics

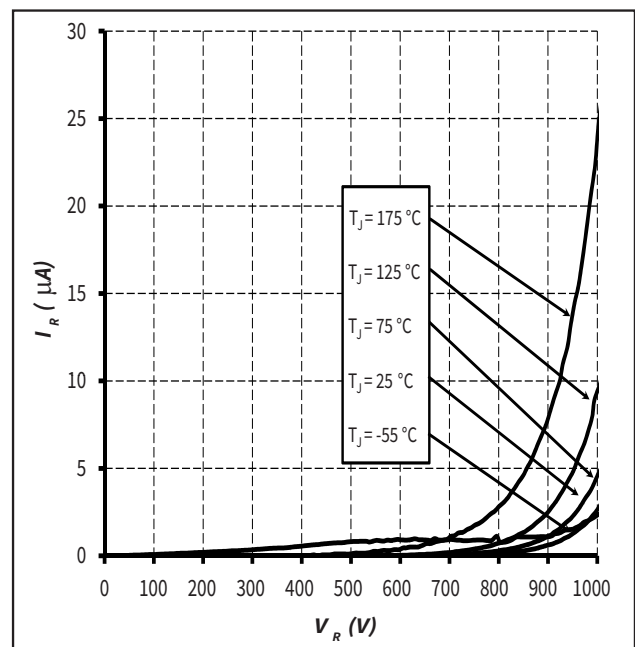


Figure 2. Reverse Characteristics



Typical Performance

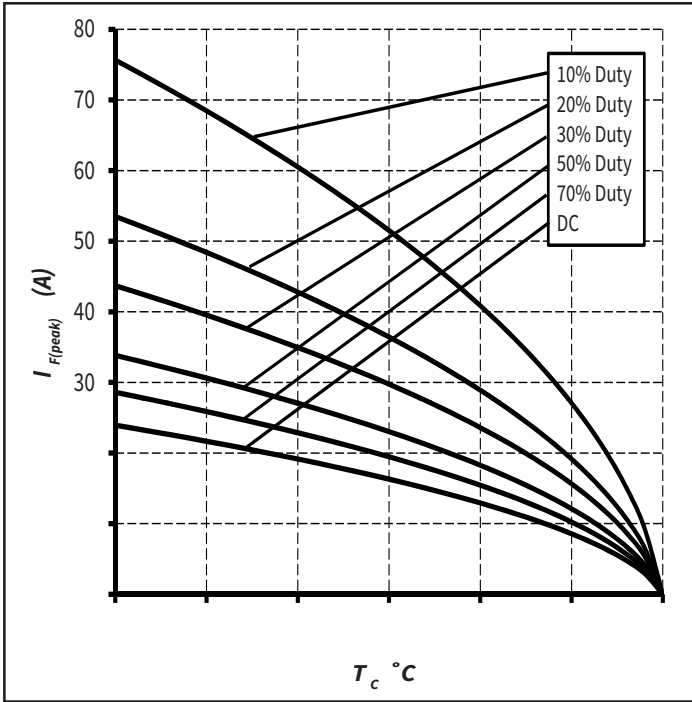


Figure 3. Current Derating

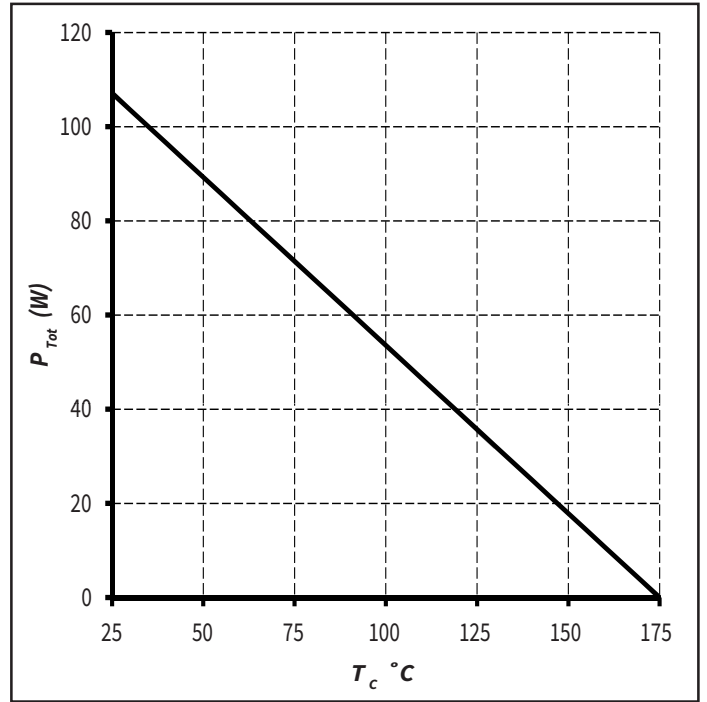


Figure 4. Power Derating

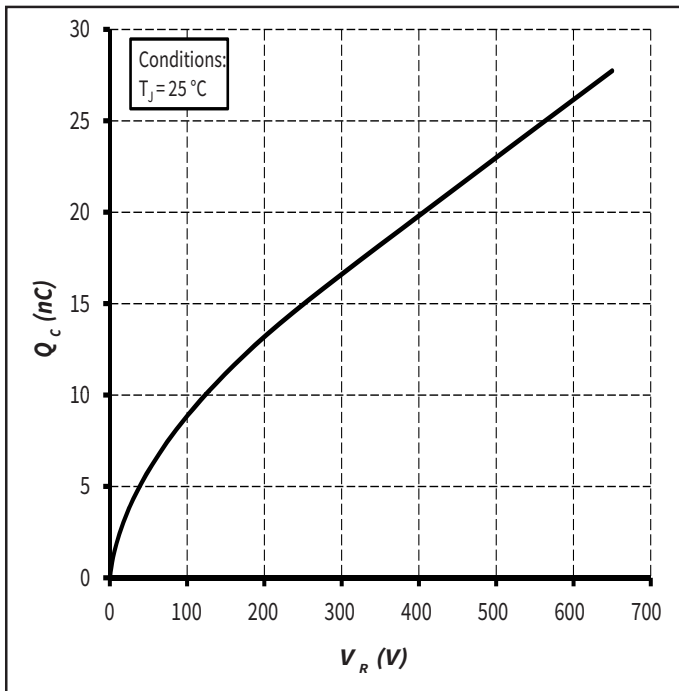


Figure 5. Total Capacitance Charge vs. Reverse Voltage

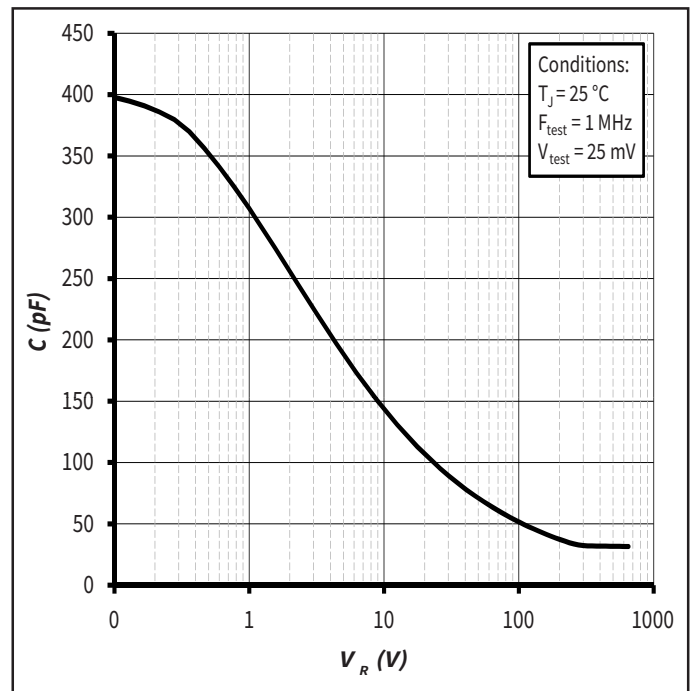


Figure 6. Capacitance vs. Reverse Voltage



Typical Performance

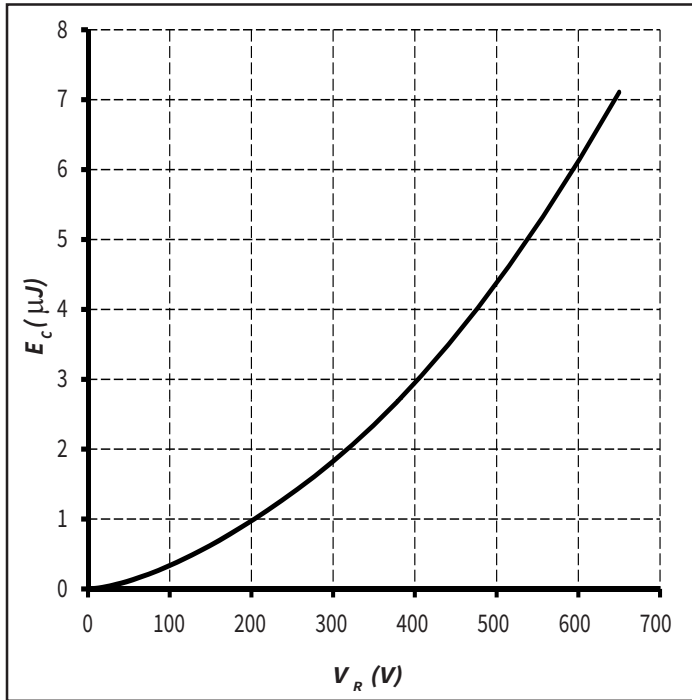


Figure 7. Capacitance Stored Energy

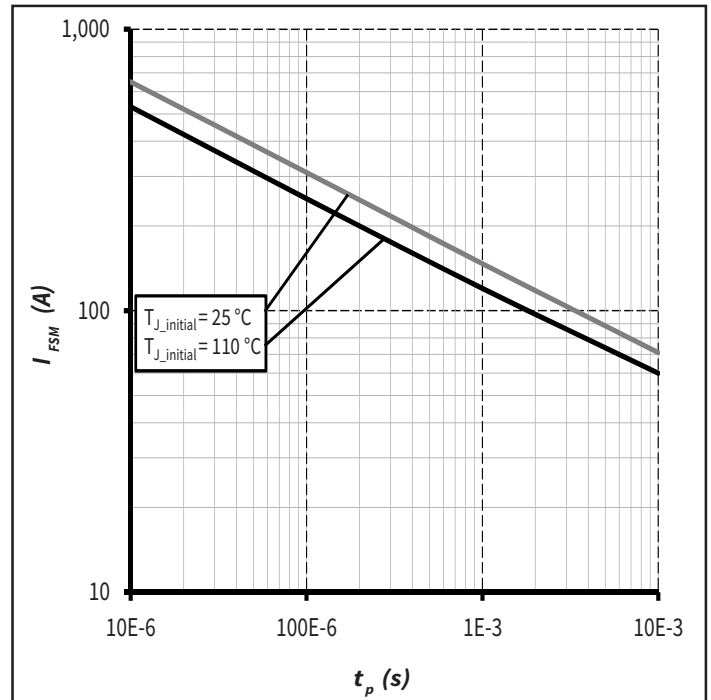


Figure 8. Non-Repetitive Peak Forward Surge Current Versus Pulse Duration (Sinusoidal Waveform)

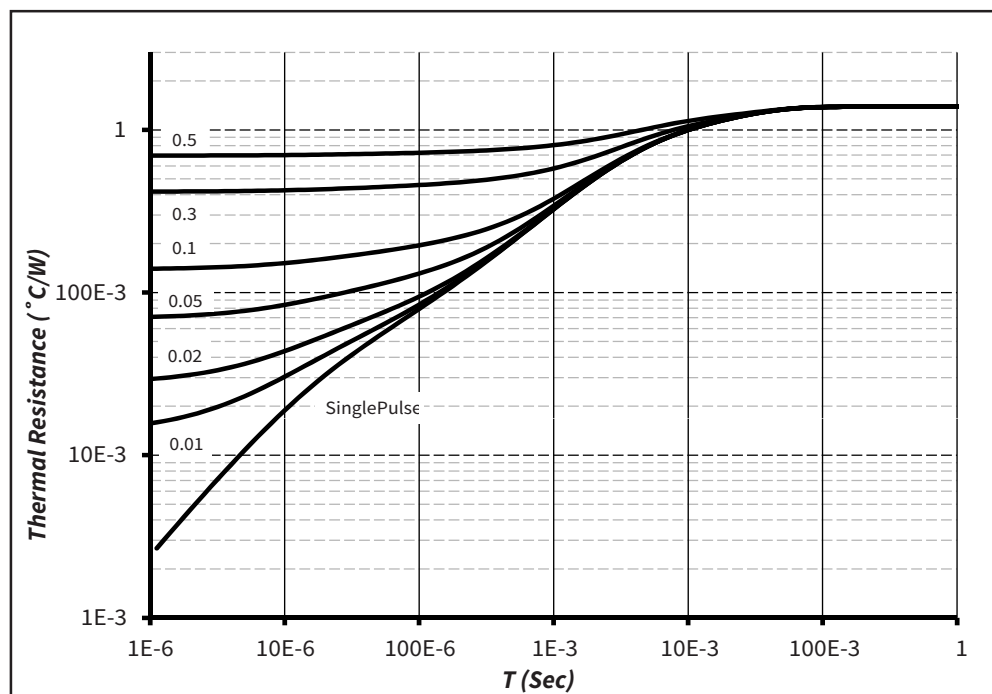
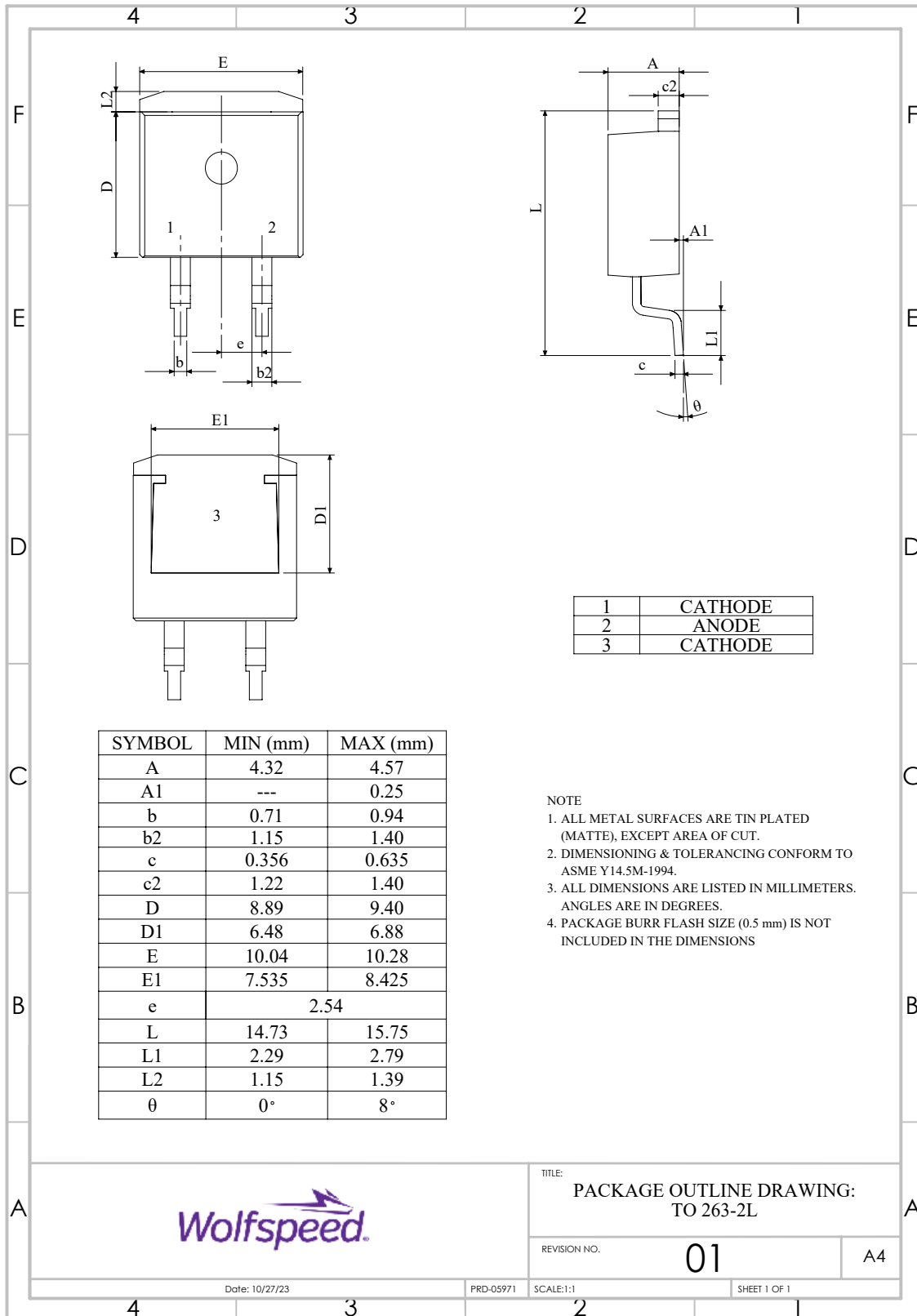


Figure 9. Transient Thermal Impedance



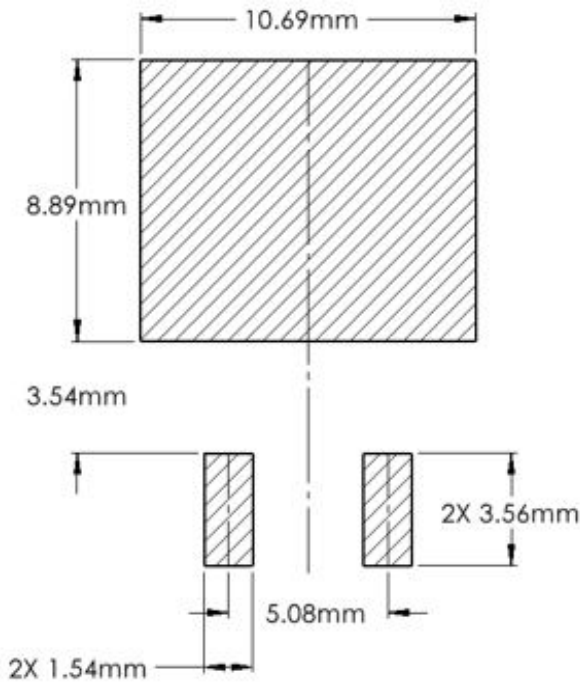
Package Dimensions

Package: TO-263-2



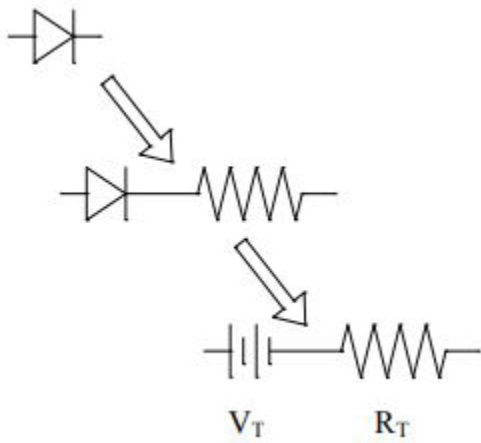


Recommended Solder Pad Layout



Part Number	Package	Marking
C3D08060G	TO-263-2	C3D08060

Diode Model



$$V_{f_T} = V_T + I_f * R_T$$

$$V_T = 0.95 + (T_j * -1.2 * 10^{-3})$$

$$R_T = 0.054 + (T_j * 5.5 * 10^{-4})$$

Note: T_j = Diode Junction Temperature In Degrees Celsius
valid from 25°C to 175°C



Revision History

Current Revision	Date of Release	Description of Changes
H	January-2018	Initial Release
11	October-2023	Updated Wolfspeed branding, package drawing, package image, and solder pad layout (Not Released)
12	November-2023	Corrected Package Drawing L and L1



Notes & Disclaimer

This document and the information contained herein are subject to change without notice. Any such change shall be evidenced by the publication of an updated version of this document by Wolfspeed. No communication from any employee or agent of Wolfspeed or any third party shall effect an amendment or modification of this document. No responsibility is assumed by Wolfspeed for any infringement of patents or other rights of third parties which may result from use of the information contained herein. No license is granted by implication or otherwise under any patent or patent rights of Wolfspeed.

Notwithstanding any application-specific information, guidance, assistance, or support that Wolfspeed may provide, the buyer of this product is solely responsible for determining the suitability of this product for the buyer's purposes, including without limitation for use in the applications identified in the next bullet point, and for the compliance of the buyers' products, including those that incorporate this product, with all applicable legal, regulatory, and safety-related requirements.

This product has not been designed or tested for use in, and is not intended for use in, applications in which failure of the product would reasonably be expected to cause death, personal injury, or property damage, including but not limited to equipment implanted into the human body, life-support machines, cardiac defibrillators, and similar emergency medical equipment, aircraft navigation, communication, and control systems, aircraft power and propulsion systems, air traffic control systems, and equipment used in the planning, construction, maintenance, or operation of nuclear facilities.

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented January 2, 2013. RoHS Declarations for this product can be obtained from your Wolfspeed representative or from the Product Documentation sections of www.wolfspeed.com.

REACH Compliance



REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact your Wolfspeed representative to ensure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

Contact info:

4600 Silicon Drive
Durham, NC 27703 USA
Tel: +1.919.313.5300
www.wolfspeed.com/power

Looking for pricing, stock, or lifecycle information?

Click below to explore more details on WIN SOURCE:

-  [View C3D08060G-TR on WIN SOURCE](#)
-  [Cree/Wolfspeed Information](#)

Optimize Your Supply Chain with WIN SOURCE Solutions

-  Global Sourcing Solution
-  Obsolete Management
-  Cost Control Management
-  Shortage Management
-  Alternative Solution
-  Excess Inventory Management